

SANYO Semiconductors DATA SHEET

N-Channel Silicon MOSFET

MCH3479 — General-Purpose Switching Device Applications

Features

- ON-resistance RDS(on)1=49m Ω (typ.)
- · 1.8V drive
- · Halogen free compliance
- · Protection diode in

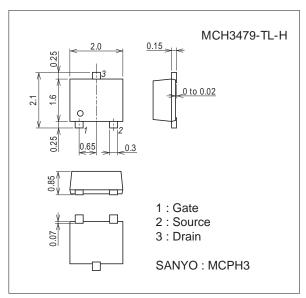
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		20	V
Gate-to-Source Voltage	VGSS		±12	V
Drain Current (DC)	ID		3.5	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	14	Α
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² ×0.8mm)	0.9	W
Channel Temperature	Tch		150	C
Storage Temperature	Tstg		-55 to +150	C

Package Dimensions

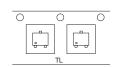
unit : mm (typ) 7019A-003



Product & Package Information

Package : MCPH3
 JEITA, JEDEC : SC-70, SOT-323
 Minimum Packing Quantity : 3,000 pcs./reel

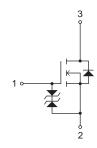
Packing Type: TL



Marking



Electrical Connection

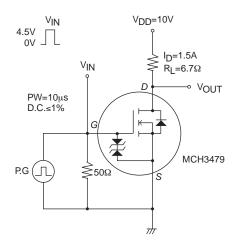


MCH3479

Electrical Characteristics at Ta=25°C

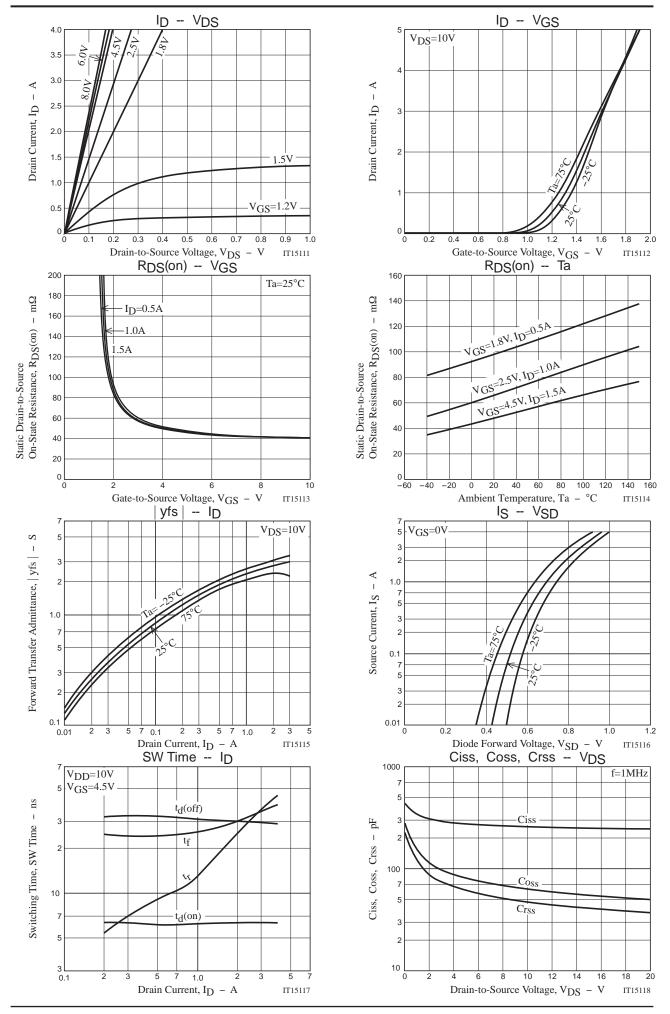
Parameter	Symbol	Conditions	Ratings			Unit	
Farameter	Symbol		min	typ	max	Uill	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	20			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0V			1	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	0.4		1.3	V	
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =1.5A		2.8		S	
	R _{DS} (on)1	I _D =1.5A, V _G S=4.5V		49	64	mΩ	
Static Drain-to-Source On-State Resistance	R _{DS} (on)2	I _D =1A, V _G S=2.5V		68	95	mΩ	
	R _{DS} (on)3	I _D =0.5A, V _G S=1.8V	99		149	mΩ	
Input Capacitance	Ciss			260		pF	
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		65		pF	
Reverse Transfer Capacitance	Crss			50		pF	
Turn-ON Delay Time	t _d (on)			6.2		ns	
Rise Time	t _r	Considered Total Circuit		19		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		30		ns	
Fall Time	tf			28		ns	
Total Gate Charge	Qg			2.8		nC	
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =4.5V, I _D =3.5A		0.6		nC	
Gate-to-Drain "Miller" Charge	Qgd]		0.9		nC	
Diode Forward Voltage	V _{SD}	I _S =3.5A, V _{GS} =0V		0.85	1.2	V	

Switching Time Test Circuit

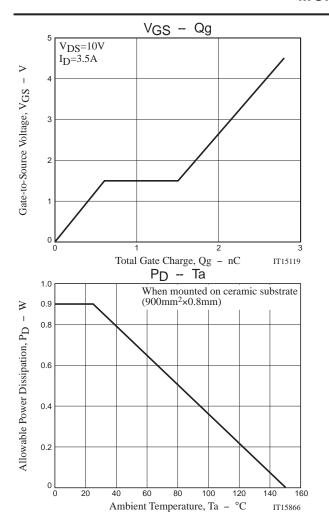


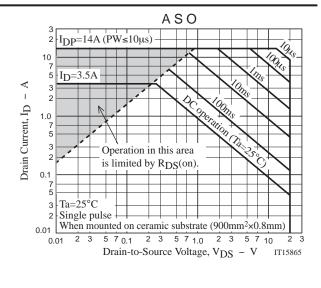
Ordering Information

Device	Package	Shipping	memo		
MCH3479-TL-H	MCPH3	3,000pcs./reel	Pb Free and Halogen Free		



MCH3479



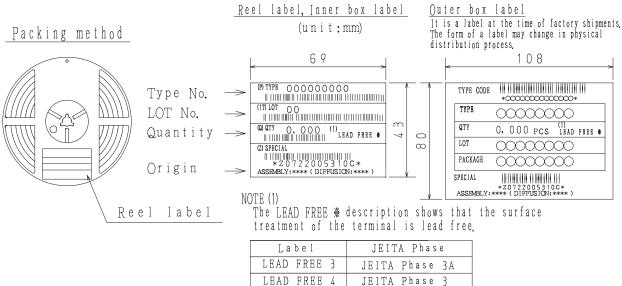


Taping Specification

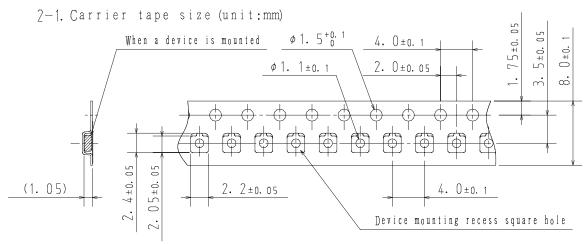
MCH3479-TL-H

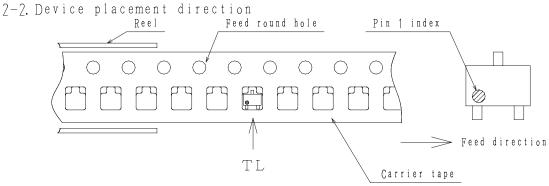
1. Packing Format

Package Name	Carrier Tape	Maximun Number of devices contained (pcs)			Packing format		
	Туре	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)	
мсрн3	мсрн3	3,000	15, 000	90,000	5 reels contained	6 inner boxes contained	
					Dimensions:mm (external)	Dimensions:mm (external)	
					183×72×185	440×195×210	



2. Taping configuration





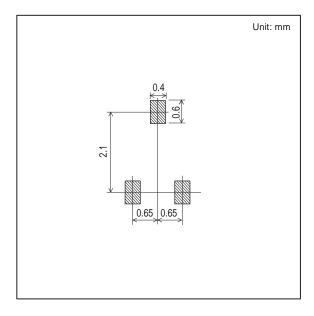
Those with pin 1 index on the feed hole side·····TL

Outline Drawing

MCH3479-TL-H

Mass (g) Unit 0.007 For reference mm 2.0+0.05 2.0+0.05 2.0+0.05 2.0+0.05 2.0+0.05 2.0+0.05 3.0+0.05 2.0+0.05 3.0+0.05 4.1:Let indication

Land Pattern Example



Note on usage: Since the MCH3479 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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